

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
Application Number		Not Yet Assigned	
Filing Date		Herewith	
First Named Inventor		Jonathan Doan	
Group Art Unit		Not Yet Assigned	
Examiner Name		Not Yet Assigned	
Attorney Docket Number		P119-US	

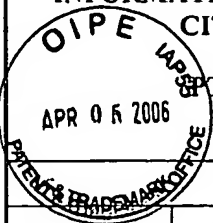
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
	DL	WINTERS, H.F., "Etch Products from the Reaction of XeF ₂ with SiO ₂ , SiO ₃ , Si ₃ N ₄ , SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	
	OU	WINTERS et al., "The Etching of Silicon with XeF ₂ Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
	DN	XACTIX, Inc., Marketing Brochure (June 27, 1999).	
	DO	"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
	DP	Assorted promotional literature, Surface Technology Systems Ltd., Newport, UK (July 28, 1999).	
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		G.J. van Gurp, et al., Aluminum-silicide reactions. II. Diffusion, compound formation, and microstructure. 1979 American Institute of Physics, pgs 6915-6922.	
		J. Baglin, et al., An Alternative marker experiment in the formation of Mo and W silicides, 1978 American Institute of Physics, pgs 289-290.	
		M. Barur, et al., Electrical characteristics of Al contact to NiSi using thin W layer as a barrier., 1981 American Institute of Physics, pgs 822-824.	
		Krishna C. Saraswat, et al., Properties of Low-Pressure CVD Tungsten Silicide for MOS VLSI interconnections, 1983 IEEE, pgs 450-454 (date not available)	
	F. Mohammadi, et al., Properties of Sputtered Tungsten Silicide for MOS Integrated Circuit Applications, pgs 450-454 (date not available)		

Examiner Signature:	Date Considered:
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE CITATION  SHEET 1 OF 1		ATTY. DOCKET NO. P119-US		SERIAL NO. 10/805,610			
		APPLICANT Doan, et al.					
		FILING DATE 3/18/04		GROUP Not Yet Assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
PG	2004-0165250	08/2004	Aubuchon				
PG	2003-0080082	05-2003	Chinn, et al.				
PG	6,558,559	05-2003	Becker, et al.				
PG	6,159,851	12-2000	Chen, et al.				
PG	6,126,851	10-2000	Norwood, et al.				
PG	6,740,247	05-2004	Han, et al.				
PG	6,666,979	12-2003	Chinn, et al.				
PG	6,299,724	10-2001	Fayfield, et al.				
PG	6,518,194	02-2003	Winningham, et al.				
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER	/Patricia George/ (08/14/2006)			DATE CONSIDERED 8/14/06			

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